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(71) Applicant: TOSHIBA CERAMICS CO LTD

(72) Inventor:  
HOTATE SHIRO  
YAMAZAKI HIROSHI  
SUGAI TERUO  
TAZOE HARUO

## (54) SUSCEPTOR

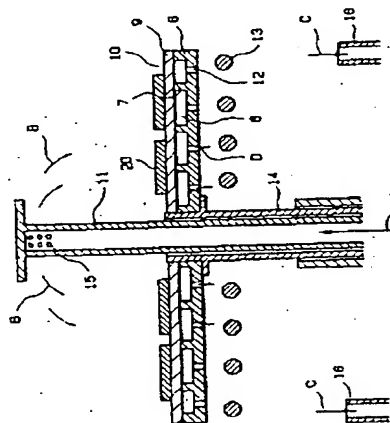
## (57) Abstract:

**PURPOSE:** To improve the quality of a wafer and lengthen its life, by providing an upper plate and a lower plate constituted of carbon molded substratum containing carbon fiber, forming hollow parts between the upper and the lower plates, and coating the surfaces of the upper and the lower plates with SiC films.

**CONSTITUTION:** A susceptor 10 is constituted of an upper plate 9 and a lower plate 8. The plates 9 and 8 are composed of carbon molded substratum containing carbon fiber. The surfaces are coated with SiC films. The plate 9 and the plate 8 are bonded with thermosetting resin based adhesive agent. Gaps (hollow parts) 6 bordered by ribs 7 are formed between the plates 9 and 8, and a holes 12 lead to the gaps 6. That is, by making the inside of the susceptor 10 hollow, temperature irregularities of a wafer mounting surface of the susceptor upper surface can be reduced, so that the fraction defective of wafer can be decreased. By coating the inner and the outer surfaces of the hollow susceptor substratum with SiC films, the generation of impurities gas is restrained, and the fraction defective can be further decreased. When holes are formed in the

lower surface of the carbon substratum the influence of the impurities gas can be further decreased.

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SiC - Film überflächte  
zum Halten der  
Bohrer & keine offene  
Poren  
Vermeidung des durch  
Porenströmung verursachten  
-> gebildeten Abgas